

ABSTRACT

A silicon single crystal wafer grown by the CZ method, which is doped with nitrogen and has an N-region for the entire plane and an interstitial oxygen concentration of 8 ppma or less, or which is doped with nitrogen and has an interstitial oxygen concentration of 8 ppma or less, and in which at least void type defects and dislocation clusters are eliminated from the entire plane, and a method for producing the same. Thus, there are provided a defect-free silicon single crystal wafer having an N-region for the entire plane, in which void type defects and dislocation clusters are eliminated, produced by the CZ method under readily controllable stable production conditions with a wide controllable range, and a method producing the same.